

PU4320

Silicon NPN/PNP Planar Darlington Type

Power Amplifier, Switching

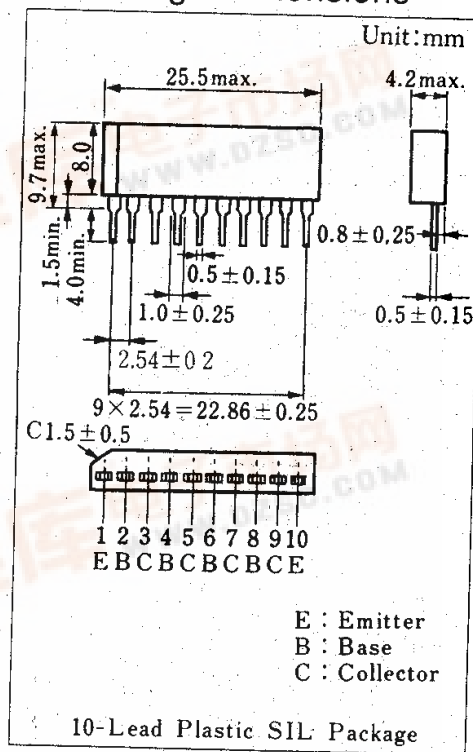
■ Features

- High DC current gain (h_{FE})
- High speed switching
- 2 NPN elements + 2 PNP elements

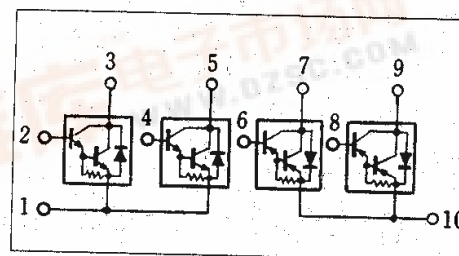
■ Absolute Maximum Ratings ($T_c=25^\circ\text{C}$)

Item	Symbol	Value	Unit
Collector-base voltage	V_{CB0}	± 60	V
Collector-emitter voltage	V_{CEO}	± 60	V
Emitter-base voltage	V_{EBO}	± 5	V
Peak collector current	I_{CP}	± 8	A
Collector current	I_C	± 4	A
Power dissipation	P_D	15	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	$-55 \sim +150$	$^\circ\text{C}$

■ Package Dimensions



■ Inner Circuit



Electrical Characteristics ($T_c=25^\circ\text{C}$)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I_{CB0}	$V_{CB} = \pm 60\text{V}, I_E = 0$			± 200	μA
	I_{CE0}	$V_{CE} = \pm 30\text{V}, I_B = 0$			± 500	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = \pm 5\text{V}, I_C = 0$			± 2	mA
Collector-emitter voltage	V_{CEO}	$I_C = \pm 30\text{mA}, I_B = 0$	± 60			V
Current gain	h_{FE1}	$V_{CE} = \pm 3\text{V}, I_C = \pm 0.5\text{A}$	1000			
	h_{FE2}^*	$V_{CE} = \pm 3\text{V}, I_C = \pm 3\text{A}$	1000		10000	
Base-emitter voltage	V_{BE}	$V_{CE} = \pm 3\text{V}, I_C = \pm 3\text{A}$			± 2.5	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = \pm 3\text{A}, I_B = \pm 12\text{mA}$			± 2	V
Transition frequency	f_T	$V_{CE} = 10\text{V}, I_C = 0.5\text{A}, f = 1\text{MHz}$		20		MHz
Turn-on time	t_{on}	$I_C = \pm 3\text{A}, I_{B1} = \pm 12\text{mA}, I_{B2} = \mp 12\text{mA}$			(typ.) NPN: 0.5, PNP: 0.3	μs
Storage time	t_{stg}				(typ.) NPN: 4, PNP: 2	μs
Fall time	t_f				(typ.) NPN: 1, PNP: 0.5	μs